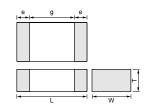
Monolithic Ceramic Capacitors GR_R6/R7/F5/E4 (X5R/X7R/Y5V/Z5U)

High Dielectric Constant Type 6.3/16/25/50V





Part Number	Dimensions (mm)						
Part Number	L	W	T	е	g min.		
GRM155	1.0 ±0.05	0.5 ±0.05	0.5 ±0.05	0.15 to 0.3	0.4		
GRM188*	1.6 ±0.1	0.8 ±0.1	0.8 ± 0.1	0.2 to 0.5	0.5		
GRM216			0.6 ± 0.1				
GRM219	2.0 ±0.1	1.25 ±0.1	0.85 ±0.1	0.2 to 0.7	0.7		
GRM21B			1.25 ±0.1				
GRM319	2 2 10 15	1.6 ±0.15	0.85 ±0.1				
GRM31M	3.2 ±0.13	1.0 ±0.13	1.15 ±0.1	0.3 to 0.8	1.5		
GRM31C	3.2 ±0.2	1.6 ±0.2	1.6 ±0.2				

^{*} Bulk Case: 1.6 ±0.07(L) × 0.8 ±0.07(W) × 0.8 ±0.07(T)

Part Number	TC Code	Rated Voltage (Vdc)	Capacitance*	Length L (mm)	Width W (mm)	Thickness T (mm)
GRM155R61A683KA01	X5R (EIA)	10	68000pF±10%	1.0	0.5	0.50
GRM155R61A104KA01	,		1.0	0.5	0.50	
GRM188R61A334KA61	X5R (EIA)	10	0.33 μF±10%	1.6	0.8	0.80
GRM188R61A474KA61	X5R (EIA)	10	0.47μF±10%	1.6	0.8	0.80
GRM188R61A684KA61	X5R (EIA)	10	0.68μF±10%	1.6	0.8	0.80
GRM188R61A105KA61	X5R (EIA)	10	1μF ±10%	1.6	0.8	0.80
GRM188R60J105KA01	X5R (EIA)	6.3	1μF ±10%	1.6	0.8	0.80
GRM219R61A105KC01	X5R (EIA)	10	1μF ±10%	2.0	1.25	0.90
GRM21BR61A225KA01	X5R (EIA)	10	2.2μF ±10%	2.0	1.25	1.25
GRM219R60J155KC01	X5R (EIA)	6.3	1.5μF ±10%	2.0	1.25	0.90
GRM21BR60J225KA01	X5R (EIA)	6.3	2.2μF ±10%	2.0	1.25	1.25
GRM21BR60J335KA11	X5R (EIA)	6.3	3.3μF ±10%	2.0	1.25	1.25
GRM21BR60J475KA11	X5R (EIA)	6.3	4.7μF ±10%	2.0	1.25	1.25
GRM319R61A225KC01	X5R (EIA)	10	2.2μF ±10%	3.2	1.6	0.90
GRM31XR61A335KC12	X5R (EIA)	10	3.3μF ±10%	3.2	1.6	1.30
GRM31CR61A475KA01	X5R (EIA)	10	4.7μF ±10%	3.2	1.6	1.60
GRM31MR60J475KC11	X5R (EIA)	6.3	4.7μF ±10%	3.2	1.6	1.15
GRM31CR61A106KA01	X5R (EIA)	10	10μF ±10%	3.2	1.6	1.60
GRM31CR60J106KA01	X5R (EIA)	6.3	10μF ±10%	3.2	1.6	1.60
GRM31CR60J226ME20	X5R (EIA)	6.3	22μF ±20%	3.2	1.6	1.60
GRM32ER61A106KC01	X5R (EIA)	10	10μF ±10%	3.2	2.5	2.50
GRM55DR61H106KA01	X5R (EIA)	50	10μF ±10%	5.7	5.0	2.00
GRM15XR71H221KA86	X7R (EIA)	50	220pF±10%	1.0	0.5	0.25
GRM155R71H221KA01	X7R (EIA)	50	220pF±10%	1.0	0.5	0.50
GRM15XR71H331KA86	X7R (EIA)	50	330pF±10%	1.0	0.5	0.25
GRM155R71H331KA01	X7R (EIA)	50	330pF±10%	1.0	0.5	0.50
GRM15XR71H471KA86	X7R (EIA)	50	470pF±10%	1.0	0.5	0.25
GRM155R71H471KA01	X7R (EIA)	50	470pF±10%	1.0	0.5	0.50
GRM15XR71H681KA86	X7R (EIA)	50	680pF±10%	1.0	0.5	0.25
GRM155R71H681KA01	X7R (EIA)	50	680pF±10%	1.0	0.5	0.50
GRM15XR71H102KA86	X7R (EIA)	50	1000pF±10%	1.0	0.5	0.25
GRM155R71H102KA01	X7R (EIA)	50	1000pF±10%	1.0	0.5	0.50
GRM15XR71H152KA86	X7R (EIA)	50	1500pF±10%	1.0	0.5	0.25
GRM155R71H152KA01	X7R (EIA)	50	1500pF±10%	1.0	0.5	0.50
GRM155R71H222KA01	X7R (EIA)	50	2200pF±10%	1.0	0.5	0.50



Part Number	TC Code	Rated Voltage (Vdc)	Capacitance*	Length L (mm)	Width W (mm)	Thickness (mm)
GRM155R71H332KA01	X7R (EIA)	50	3300pF±10%	1.0	0.5	0.50
GRM155R71H472KA01	X7R (EIA)	50	4700pF±10%	1.0	0.5	0.50
GRM15XR71E182KA86	X7R (EIA)	25	1800pF±10%	1.0	0.5	0.25
RM15XR71E222KA86	X7R (EIA)	25	2200pF±10%	1.0	0.5	0.25
RM155R71E682KA01	X7R (EIA)	25	6800pF±10%	1.0	0.5	0.50
RM155R71E103KA01	X7R (EIA)	25	10000pF±10%	1.0	0.5	0.50
GRM15XR71C332KA86	X7R (EIA)	16	3300pF±10%	1.0	0.5	0.25
GRM15XR71C472KA86	X7R (EIA)	16	4700pF±10%	1.0	0.5	0.25
GRM15XR71C682KA86	X7R (EIA)	16	6800pF±10%	1.0	0.5	0.25
GRM155R71C153KA01	X7R (EIA)	16	15000pF±10%	1.0	0.5	0.50
GRM155R71C223KA01	X7R (EIA)	16	22000pF±10%	1.0	0.5	0.50
GRM155R71A333KA01	X7R (EIA)	10	33000pF±10%	1.0	0.5	0.50
GRM155R71A473KA01	X7R (EIA)	10	47000pF±10%	1.0	0.5	0.50
GRM188R71H221KA01	X7R (EIA)	50	220pF±10%	1.6	0.8	0.80
GRM188R71H331KA01	X7R (EIA)	50	330pF±10%	1.6	0.8	0.80
GRM188R71H471KA01	X7R (EIA)	50	470pF±10%	1.6	0.8	0.80
GRM188R71H681KA01	X7R (EIA)	50	680pF±10%	1.6	0.8	0.80
GRM188R71H102KA01	X7R (EIA)	50	1000pF±10%	1.6	0.8	0.80
GRM188R71H152KA01	X7R (EIA)	50	1500pF±10%	1.6	0.8	0.80
GRM188R71H222KA01	X7R (EIA)	50	2200pF±10%	1.6	0.8	0.80
GRM188R71H332KA01	X7R (EIA)	50	3300pF±10%	1.6	0.8	0.80
GRM188R71H472KA01	X7R (EIA)	50	4700pF±10%	1.6	0.8	0.80
GRM188R71H682KA01	X7R (EIA)	50	6800pF±10%	1.6	0.8	0.80
GRM188R71H103KA01	X7R (EIA)	50	10000pF±10%	1.6	0.8	0.80
GRM188R71H153KA01	X7R (EIA)	50	15000pF±10%	1.6	0.8	0.80
GRM188R71H223KA01	X7R (EIA)	50	22000pF±10%	1.6	0.8	0.80
GRM188R71E333KA01	X7R (EIA)	25	33000pF±10%	1.6	0.8	0.80
SRM188R71E473KA01	X7R (EIA)	25	47000pF±10%	1.6	0.8	0.80
GRM188R71E683KA01	X7R (EIA)	25	68000pF±10%	1.6	0.8	0.80
GRM188R71E104KA01	X7R (EIA)	25	0.1μF±10%	1.6	0.8	0.80
GRM188R71C104KA01	X7R (EIA)	16	0.1μF±10%	1.6	0.8	0.80
GRM188R71A154KA01	X7R (EIA)	10	0.15μF±10%	1.6	0.8	0.80
GRM188R71A224KA01	X7R (EIA)	10	22000pF±10%	1.6	0.8	0.80
GRM219R71H333KA01	X7R (EIA)	50	33000pF±10%	2.0	1.25	0.90
GRM21BR71H473KA01	X7R (EIA)	50	47000pF±10%	2.0	1.25	1.25
GRM21BR71H683KA01	X7R (EIA)	50	68000pF±10%	2.0	1.25	1.25
GRM21BR71H104KA01	X7R (EIA)	50	0.1μF±10%	2.0	1.25	1.25
GRM21BR71H154KA01	X7R (EIA)	50	0.15μF±10%	2.0	1.25	1.25
GRM21BR71H224KA01	X7R (EIA)	50	22000pF±10%	2.0	1.25	1.25
GRM21BR71E104KA01	X7R (EIA)	25	0.1μF±10%	2.0	1.25	1.25
GRM21BR71E154KA01	X7R (EIA)	25	0.15μF±10%	2.0	1.25	1.25
GRM219R71E224KC01	X7R (EIA)	25	22000pF±10%	2.0	1.25	0.90
GRM21BR71E334KC01	X7R (EIA)	25	0.33 μF±10%	2.0	1.25	1.25
GRM21BR71E474KC01	X7R (EIA)	25	0.47μF±10%	2.0	1.25	1.25
GRM219R71C474KC01	X7R (EIA)	16	0.47μF±10%	2.0	1.25	0.90
GRM219R71C684KC01	X7R (EIA)	16	0.47μ1±10% 0.68μF±10%	2.0	1.25	0.90
GRM21BR71C105KA01	X7R (EIA)	16	0.08μ1±10% 1μF ±10%	2.0	1.25	1.25
GRM319R71H334KA01	X7R (EIA)	50	0.33 μF±10%	3.2	1.6	0.90
GRM31MR71H474KA01	X7R (EIA)	50	0.33 μF±10% 0.47μF±10%	3.2	1.6	1.15
		25	·	3.2	1.6	
GRM319R71E684KC01	X7R (EIA)		0.68μF±10%			0.90
GRM31MR71E105KC01	X7R (EIA)	25	1μF ±10%	3.2	1.6	1.15
GRM319R71C105KC11	X7R (EIA)	16	1μF ±10%	3.2	1.6	0.90
GRM31MR71C155KC11	X7R (EIA)	16	1.5μF ±10%	3.2	1.6	1.15
GRM31MR71C225KA35	X7R (EIA)	16	2.2μF ±10%	3.2	1.6	1.15



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Continued from the preceding page.

Part Number	TC Code	Rated Voltage (Vdc)	Capacitance*	Length L (mm)	Width W (mm)	Thickness (mm)
GRM319R71A225KA01	X7R (EIA)	10	2.2μF ±10%	3.2	1.6	0.90
GRM32NR71H684KA01	X7R (EIA)	50	0.68μF±10%	3.2	2.5	1.35
GRM32RR71H105KA01	X7R (EIA)	50	1μF ±10%	3.2	2.5	1.80
GRM32RR71E225KC01	X7R (EIA)	25	2.2μF ±10%	3.2	2.5	1.80
GRM32MR71C225KC01	X7R (EIA)	16	2.2μF ±10%	3.2	2.5	1.15
RM32NR71C335KC01	X7R (EIA)	16	3.3μF ±10%	3.2	2.5	1.35
GRM32RR71C475KC01	X7R (EIA)	16	4.7μF ±10%	3.2	2.5	1.80
GRM43ER71H225KA01	X7R (EIA)	50	2.2μF ±10%	4.5	3.2	2.50
GRM55RR71H105KA01	X7R (EIA)	50	1μF ±10%	5.7	5.0	1.80
GRM55RR71H155KA01	X7R (EIA)	50	1.5μF ±10%	5.7	5.0	1.80
GRM155F51H222ZA01	Y5V (EIA)	50	2200pF +80%, -20%	1.0	0.5	0.50
GRM155F51H472ZA01	Y5V (EIA)	50	4700pF +80%, -20%	1.0	0.5	0.50
GRM155F51H103ZA01	Y5V (EIA)	50	10000pF +80%, -20%	1.0	0.5	0.50
GRM155F51E223ZA01	Y5V (EIA)	25	22000pF +80%, -20%	1.0	0.5	0.50
GRM155F51C473ZA01	Y5V (EIA)	16	47000pF +80%, -20%	1.0	0.5	0.50
GRM155F51C104ZA01	Y5V (EIA)	16	10000pF +80%, -20%	1.0	0.5	0.50
GRM188F51H103ZA01	Y5V (EIA)	50	10000pF +80%, -20%	1.6	0.8	0.80
GRM188F51H223ZA01	Y5V (EIA)	50	22000pF +80%, -20%	1.6	0.8	0.80
GRM188F51H473ZA01	Y5V (EIA)	50	47000pF +80%, -20%	1.6	0.8	0.80
GRM188F51H104ZA01	Y5V (EIA)	50	10000pF +80%, -20%	1.6	0.8	0.80
GRM188F51E104ZA01	Y5V (EIA)	25	10000pF +80%, -20%	1.6	0.8	0.80
GRM188F51C224ZA01	Y5V (EIA)	16	22000pF +80%, -20%	1.6	0.8	0.80
GRM188F51C474ZA01	Y5V (EIA)	16	0.47µF +80%, -20%	1.6	0.8	0.80
GRM188F51A474ZC01	Y5V (EIA)	10	0.47µF +80%, -20%	1.6	0.8	0.80
GRM188F51A105ZA01	Y5V (EIA)	10	1μF +80%, -20%	1.6	0.8	0.80
GRM219F51H104ZA01	Y5V (EIA)	50	10000pF +80%, -20%	2.0	1.25	0.90
GRM21BF51H224ZA01	Y5V (EIA)	50	22000pF +80%, -20%	2.0	1.25	1.25
GRM219F51E224ZA01	Y5V (EIA)	25	22000pF +80%, -20%	2.0	1.25	0.90
GRM21BF51E474ZA01	Y5V (EIA)	25	0.47μF +80%, -20%	2.0	1.25	1.25
GRM219F51E105ZA01	, ,	25	1μF +80%, -20%	2.0		0.90
	Y5V (EIA)		2.2μF +80%, -20%		1.25	
GRM21BF51E225ZA01	Y5V (EIA)	25		2.0	1.25	1.25
GRM219F51C105ZA01	Y5V (EIA)	16	1μF +80%, -20%	2.0	1.25	0.90
GRM21BF51C225ZA01	Y5V (EIA)	16	2.2μF +80%, -20%	2.0	1.25	1.25
GRM219F51A105ZA01	Y5V (EIA)	10	1μF +80%, -20%	2.0	1.25	0.90
GRM21BF51A225ZA01	Y5V (EIA)	10	2.2μF +80%, -20%	2.0	1.25	1.25
GRM21BF51A475ZA01	Y5V (EIA)	10	4.7μF +80%, -20%	2.0	1.25	1.25
GRM31MF51H474ZA01	Y5V (EIA)	50	0.47μF +80%, -20%	3.2	1.6	1.15
GRM31MF51E105ZA01	Y5V (EIA)	25	1μF +80%, -20%	3.2	1.6	1.15
GRM31MF51E475ZA01	Y5V (EIA)	25	4.7μF +80%, -20%	3.2	1.6	1.15
GRM319F51C105ZA01	Y5V (EIA)	16	1μF +80%, -20%	3.2	1.6	0.90
GRM31MF51C225ZA01	Y5V (EIA)	16	2.2μF +80%, -20%	3.2	1.6	1.15
GRM31MF51C475ZA12	Y5V (EIA)	16	4.7μF +80%, -20%	3.2	1.6	1.15
GRM319F51A225ZA01	Y5V (EIA)	10	2.2μF +80%, -20%	3.2	1.6	0.90
GRM31MF51A475ZA01	Y5V (EIA)	10	4.7μF +80%, -20%	3.2	1.6	1.15
GRM31MF51A106ZA01	Y5V (EIA)	10	10μF +80%, -20%	3.2	1.6	1.15
GRM31MF50J106ZA01	Y5V (EIA)	6.3	10μF +80%, -20%	3.2	1.6	1.15
GRM32RF51H105ZA01	Y5V (EIA)	50	1μF +80%, -20%	3.2	2.5	1.80
GRM329F51E475ZA01	Y5V (EIA)	25	4.7μF +80%, -20%	3.2	2.5	0.90
GRM32NF51E106ZA01	Y5V (EIA)	25	10μF +80%, -20%	3.2	2.5	1.35
GRM32NF51C106ZA01	Y5V (EIA)	16	10μF +80%, -20%	3.2	2.5	1.35
GRM188E41H103MA01	Z5U (EIA)	50	10000pF±20%	1.6	0.8	0.80
GRM188E41H223MA01	Z5U (EIA)	50	22000pF±20%	1.6	0.8	0.80
GRM216E41H473MA01	Z5U (EIA)	50	47000pF±20%	2.0	1.25	0.60
GRM219E41H104MA01	Z5U (EIA)	50	10000pF±20%	2.0	1.25	0.90
GRM319E41H224MA01	Z5U (EIA)	50	22000pF±20%	3.2	1.6	0.90

Note • This catalog has only typical specifications because there is no space for detailed specifications. Therefore, please approve our product specification or transact the approval sheet for product specification before ordering. Especially, please read rating and
 \(\triangle \) CAUTION (for storage and operating, rating, soldering and mounting, handling) in them to prevent smoking and/or burning, etc.

 You are able to read a detailed specification in the website (http://search.murata.co.jp/) before to require our product specification or to transact the approval sheet for product specification.

Capacitors muRata

■ Specifications and Test Methods

		Specifi	ications				
No.	Item	Temperature Compensating Type	High Dielectric Type	Test Method			
1	Operating Temperature Range	-55 to +125℃	B1, B3, F1 : -25°C to +85°C R1, R7 : -55°C to +125°C E4 : +10°C to +85°C F5 : -30°C to +85°C	Reference Temperature : 25℃ (2∆, 3∆, 4∆, B1, B3, F1, R1 : 20℃)			
2	Rated Voltage	See the previous pages		The rated voltage is defined as the maximum voltage which may be applied continuously to the capacitor. When AC voltage is superimposed on DC voltage, $V^{\text{p-p}}$ or $V^{\text{o-p}}$, whichever is larger, should be maintained within the rated voltage range.			
3	Appearance	No defects or abnormalities		Visual inspection			
4	Dimensions	Within the specified dimensions	3	Using calipers			
5	Dielectric Strength	No defects or abnormalities		No failure should be observed when 300% of the rated voltage (temperature compensating type) or 250% of the rated voltage (high dielectric constant type) is applied between the terminations for 1 to 5 seconds, provided the charge/discharge current is less than 50mA.			
6	Insulation Resistance	C≦0.047μF : More than 10,000 C>0.047μF : 500Ω • F	MΩ C : Nominal Capacitance	The insulation resistance should be measured with a DC voltage not exceeding the rated voltage at 20°C/25°C and 75%RH max. and within 2 minutes of charging, provided the charge/discharge current is less than 50mA.			
7	Capacitance	Within the specified tolerance		The capacitance/D.F. should be measured at 20°C/25°C at the			
8	O/ Dissipation Factor (D.F.)	30pF and over : Q≥1000 30pF and below : Q≥400+20C C : Nominal Capacitance (pF)	[B1, B3, R1, R6, R7, E4] W.V.: 25Vmin.: 0.025max. W.V.: 16/10V: 0.035max. W.V.: 6.3V/4V : 0.05max. (C≤3.3μF) : 0.1max. (C≥3.3μF) [F1, F5] W.V.: 25Vmin. : 0.05max. (C≤0.1μF) : 0.09max. (C≥0.1μF) W.V.: 16V/10V: 0.125max. W.V.: 6.3V: 0.15max.	Char.			





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			Specif	ications
No	o. Ite	em	Temperature Compensating Type	High Dielectric Type
		No bias	Within the specified tolerance (Table A-1)	B1, B3 : Within±10% (-25°C to +85°C) R1, R7 : Within±15% (-55°C to +125°C) R6 : Within±15% (-55°C to +85°C) E4 : Within +22/-56% (+10°C to +85°C) F1 : Within +30/-80% (-25°C to +85°C) F5 : Within +22/-82% (-30°C to +85°C)
		50% of the Rated Voltage		B1: Within +10/-30% R1: Within +15/-40% F1: Within +30/-95%
9	Capacitance Temperature Characteristics	Capacitance Drift	Within ±0.2% or ±0.05pF (Whichever is larger.) *Not apply to 1X/25V	*Initial measurement for high dielectric constant type Perform a heat treatment at 150+0/–10°C for one hour and then set for 48±4 hours at room temperature. Perform the initial measurement.
			No removal of the terminations	or other defect should occur
10	Adhesive of Termir	: Strength nation		Solder resist Baked electrode or copper foil

Test Method

The capacitance change should be measured after 5min. at each specified temp. stage.

(1)Temperature Compensating Type

The temperature coefficient is determind using the capacitance measured in step 3 as a reference.

When cycling the temperature sequentially from step 1 through 5 (5C: $+25^{\circ}$ C to $+125^{\circ}$ C/ Δ C: $+20^{\circ}$ C to $+125^{\circ}$ C: other temp. coeffs. : +25°C to +85°C/+20°C to +85°C) the capacitance should be within the specified tolerance for the temperature coefficient and capacitance change as Table A-1.

The capacitance drift is caluculated by dividing the differences between the maximum and minimum measured values in the step 1, 3 and 5 by the cap. value in step 3.

Step	Temperature (℃)
1	Reference Temperature±2
2	-55±3 (for ΔC)/-25±3 (for other TC)
3	Reference Temperature±2
4	125±3 (for ΔC)/85±3 (for other TC)
5	Reference Temperature±2

(2) High Dielectric Constant Type

The ranges of capacitance change compared with the 20°C value over the temperature ranges shown in the table should be within the specified ranges.*

In case of applying voltage, the capacitance change should be measured after 1 more min. with applying voltage in equilibration of each temp. stage.

Step	Temperature (°C)	Applying Voltage (V)
1	Reference Tempereture±2	
2	-55±3 (for R1, R7, R6) -25±3 (for B1, B3, F1) -30±3 (for F5)/10±3 (for E4)	No bias
3	Reference Tempereture±2	INO DIAS
4	125±3 (for R1, R7)/ 85±3 (for B1, B3, R6 F1, F5, E4)	
5	Reference Tempereture±2	
6	-55±3 (for R1)/ -25±3 (for B1, F1)	50% of the rated
7	Reference Tempereture±2	voltage
8	125±3 (for R1)/ 85±3 (for B1, F1)	

Solder the capacitor to the test jig (glass epoxy board) shown in Fig. 1a using an eutectic solder. Then apply 10N* force in parallel with the test jig for 10±1 sec.

The soldering should be done either with an iron or using the reflow method and should be conducted with care so that the soldering is uniform and free of defects such as heat shock. *2N (GR□03), 5N (GR□15, GRM18)

			(in mm)
Туре	a	b	С
GR□03	0.3	0.9	0.3
GR□15	0.4	1.5	0.5
GRM18	1.0	3.0	1.2
GRM21	1.2	4.0	1.65
GRM31	2.2	5.0	2.0
GRM32	2.2	5.0	2.9
GRM43	3.5	7.0	3.7
GRM55	4.5	8.0	5.6



			Specifi	cations				
No.	Ite	em	Temperature Compensating Type	High Dielectric Type		Test Me	ethod	
		Appearance	No defects or abnormalities					
		Capacitance	Within the specified tolerance					
11	Vibration Resistance	Q/D.F.	30pF and over : Q≥1000 30pF and below : Q≥400+20C C : Nominal Capacitance (pF)	[B1, B3, R1, R6, R7, E4] W.V.: 25Vmin.: 0.025max. W.V.: 16/10V: 0.035max. W.V.: 6.3V/4V : 0.05max. (C<3.3μF) : 0.1max. (C≥3.3μF) [F1, F5] W.V.: 25Vmin. : 0.05max. (C<0.1μF) : 0.09max. (C≥0.1μF) W.V.: 16V/10V: 0.125max. W.V.: 6.3V: 0.15max.	Solder the capacitor on the test jig (glass epoxy board) in the same manner and under the same conditions as (10). The capacitor should be subjected to a simple harmonic mot having a total amplitude of 1.5mm, the frequency being varie uniformly between the approximate limits of 10 and 55Hz. The frequency range, from 10 to 55Hz and return to 10Hz, should be traversed in approximately 1 minute. This motion should I applied for a period of 2 hours in each 3 mutually perpendict directions (total of 6 hours).			as (10). has harmonic motion ncy being varied of and 55Hz. The to 10Hz, should motion should be
			No crack or marked defect shou	uld occur	in Fig. 2a using direction shown	-	r. Then apply sec. The so	y a force in the Idering should be
						ith care so that the		ethod and should s uniform and free
12	Defle	ction	R230 Capacitance n	speed : 1.0mm/sec. Pressurize R230 Flexure : ≤1 Capacitance meter 45 45			b 0.9 1.5 3.0 4.0 5.0 7.0 8.0	C 0.3 0.5 1.2 1.65 2.0 2.9 3.7 5.6 (in mm)
13	Solderabi Terminati	•	75% of the terminations are to be soldered evenly and continuously		Immerse the capacitor in a solution of ethanol (JIS-K-8101) and rosin (JIS-K-5902) (25% rosin in weight propotion) . Preheat at 80 to 120℃ for 10 to 30 seconds. After preheating, immerse in an eutectic solder solution for 2±0.5 seconds at 230±5℃.			
			The measured and observed ch specifications in the following ta	•				
		Appearance	No defects or abnormalities		_			
		Capacitance Change	Within ±2.5% or ±0.25pF (Whichever is larger)	B1, B3, R1, R6, R7 : Within ±7.5% F1, F5, E4 : Within ±20%	Immerse the car	acitor at 120 to 15 pacitor in an euteon description and set at room	ctic solder so	olution at 270±5℃
14	Resistance to Soldering Heat	Q/D.F.	30pF and over : Q≥1000 30pF and below : Q≥400+20C C : Nominal Capacitance (pF)	[B1, B3, R1, R6, R7, E4] W.V.: 25Vmin.: 0.025max. W.V.: 16/10V: 0.035max. W.V.: 6.3V/4V : 0.05max. (C<3.3μF) : 0.1max. (C≥3.3μF) [F1, F5] W.V.: 25Vmin. : 0.05max. (C<0.1μF) : 0.09max. (C≥0.1μF) W.V.: 16V/10V: 0.125max. W.V.: 6.3V: 0.15max.	(temperature co constant type), t •Initial measurer Perform a heat t then set at room	mpensating tyoe) hen measure. ment for high diele treatment at 150+ a temperature for a al measurement.	or 48±4 horectric constant of the constant of	urs (high dielectric
		I.R.	More than 10,000M Ω or 500 Ω	F (Whichever is smaller)				
		Dielectric Strength	No defects					

		Specifi	cations					
No. It	em	Temperature Compensating Type	High Dielectric Type	Test Method		ı		
		The measured and observed characteristics should safisfy the specifications in the following table						
	Appearance	No defects or abnormalities						
	Capacitance Change	Within ±2.5% or ±0.25pF (Whichever is larger)	B1, B3, R1, R6, R7 : Within ±7.5% F1, F5, E4 : Within ±20%	Fix the capacitor to the supporting jig in the same manner and under the same conditions as (10). Perform the five cycles according to the four heat treatm shown in the following table.			atments	
			[B1, B3, R1, R6, R7, E4] W.V. : 25Vmin. : 0.025max. W.V. : 16/10V : 0.035max.	Set for 24±2 he hours (high die measure.			t room tempera	
15 Temperature		30pF and over : Q≧1000	W.V.: 6.3V/4V	Step	1	2	3	4
Cycle	Q/D.F.	30pF and below : Q≧400+20C	: 0.05max. (C<3.3µF) : 0.1max. (C≧3.3µF) [F1, F5]	Temp. (℃)	Min. Operating Temp.+0/-3	Room Temp.	Max. Operating Temp.+3/-0	Room Temp.
	C : Nominal Capacita	C : Nominal Capacitance (pF)	W.V. : 25Vmin.	Time (min.)	30±3	2 to 3	30±3	2 to 3
			: 0.05max. (C<0.1µF) : 0.09max. (C≧0.1µF) W.V. : 16V/10V : 0.125max. W.V. : 6.3V : 0.15max.	•Initial measurement for high dielectric constant type Perform a heat treatment at 150+0/-10°C for one hour and then set at room temperature for 48±4 hours. Perform the initial measurement.				
	I.R.	More than 10,000M Ω or 500 Ω						
	Dielectric Strength	No defects						
		The measured and observed ch specifications in the following ta						
	Appearance	No defects or abnormalities						
	Capacitance Change	Within ±5% or ±0.5pF (Whichever is larger)	B1, B3, R1, R6, R7, C8 : Within ±12.5% F1, F5 : Within ±30%					
Humidity 16 (Steady State)	W.V.:2 30pF and over : Q≥350 W.V.:1 10pF and over W.V.:6 30pF and below : :0		[B1, B3, R1, R6, R7, E4] W.V.: 25Vmin.: 0.05max. W.V.: 16/10V: 0.05max. W.V.: 6.3V/4V : 0.075max. (C<3.3μF) : 0.125max. (C≥3.3μF)	Set the capacitor at 40±2°C and in 90 to 95% humiduty for 500±12 hours. Remove and set for 24±2 hours (temperature compensati type) or 48±4 hours (high dielectric constant type) at room temperature, then measure.			ensating	
	Q/D.F.	10pF and below : Q≥200+10C C : Nominal Capacitance (pF)	[F1, F5] W.V. : 25Vmin. : 0.075max. (C<0.1μF)					
	I.R.	More than $1,000M\Omega$ or $50\Omega \bullet F$						



			Specifi	cations			
No.	Ite	em	Temperature Compensating Type	High Dielectric Type	Test Method		
			The measured and observed characteristics should satisfy the specifications in the following table				
	A	Appearance	No defects or abnormalities				
		Capacitance Change	Within ±7.5% or ±0.75pF (Whichever is larger)	B1, B3, R1, R6, R7 : Within ±12.5% F1, F5, E4: Within ±30% [W.V.: 10Vmax.] F1, F5: Within +30/-40%	Apply the rated voltage at 40±2°C and 90 to 95% humidity for 500±12 hours. Remove and set for 24±2 hours (temperature		
17	Humidity Load	Q/D.F.	30pF and over : Q≥200 30pF and below : Q≥100+10C/3 C : Nominal Capacitance (pF)	[B1, B3, R1, R6, R7, E4] W.V.: 25Vmin.: 0.05max. W.V.: 16/10V: 0.05max. W.V.: 6.3V : 0.075max. (C<3.3μF) : 0.125max. (C≥3.3μF) [F1, F5] W.V.: 25Vmin. : 0.075max. (C<0.1μF) : 0.125max. (C≥0.1μF) W.V.: 16V/10V: 0.15max. W.V.: 6.3V: 0.2max.	500±12 hours. Remove and set for 24±2 hours (temperat compensating type) or 48±4 hours (high dielectric constar type) at room temprature, then muasure. The charge/discreared is less than 50mA. •Initial measurement for F1, F5/10V max. Apply the rated DC voltage for 1 hour at 40±2°C. Remove and set for 48±4 hours at room temperature. Perform initial measurement.		
		I.R.	More than 500MΩ or 25Ω • F (V	Vhichever is smaller)			
			The measured and observed ch specifications in the following ta				
		Appearance	No defects or abnormalities				
		Capacitance Change	Within ±3% or ±0.3pF (Whichever is larger)	B1, B3, R1, R6, R7 : Within ±12.5% F1, F5, E4: Within ±30% [Exept 10Vmax. and. C≥1.0µF] F1, F5: Within +30/−40% [10Vmax. and. C≥1.0µF]	Apply 200% of the rated voltage at the maximum operating temperature ±3°c for 1000±12 hours. Set for 24±2 hours (temperature compensating type) or 48±4 hours (high dielectric constant type) at room temperature, then measure.		
18	High Temperature Load	Q/D.F.	30pF and over : Q≥350 10pF and over 30pF and below : Q≥275+2.5C 10pF and below : Q≥200+10C C : Nominal Capacitance (pF)	[B1, B3, R1, R6, R7, E4] W.V.: 25Vmin.: 0.04max. W.V.: 16/10V: 0.05max. W.V.: 6.3V : 0.075max.(C<3.3μF) : 0.125max.(C≥3.3μF) [F1, F5] W.V.: 25Vmin. : 0.075max.(C<0.1μF) : 0.125max.(C≥0.1μF) W.V.: 16V/10V: 0.15max. W.V.: 6.3V: 0.2max.	The charge/discharge current is less than 50mA. •Initial measurement for high dielectric constant type. Apply 200% of the rated DC voltage at the maximun operating temperature ±3°C for one hour. Remove and set for 48±4 hours at room temperature. Perform initial measurement.		
		I.R.	More than 1,000M Ω or 50 Ω •F (Whichever is smaller)			



Capacitors muRata

Continued from the preceding page.

Table A-1

		Capacitance Change from 25℃ (%)					
Char.	Nominal Values (ppm/°C)*1	-55		-30		-10	
		Max.	Min.	Max.	Min.	Max.	Min.
5C	0± 30	0.58	-0.24	0.40	-0.17	0.25	-0.11
6C	0± 60	0.87	-0.48	0.59	-0.33	0.38	-0.21
6P	-150± 60	2.33	0.72	1.61	0.50	1.02	0.32
6R	-220± 60	3.02	1.28	2.08	0.88	1.32	0.56
6S	-330± 60	4.09	2.16	2.81	1.49	1.79	0.95
6T	-470± 60	5.46	3.28	3.75	2.26	2.39	1.44
7U	-750±120	8.78	5.04	6.04	3.47	3.84	2.21
1X	+350 to -1000	_	_	_	_	_	_

^{*1}Nominal values denote the temperature coefficient within a range of 25°C to 125°C (for Δ C)/85°C (for other TC).

(2)

			(Capacitance Cha	nge from 20℃ (%))	
Char.	Nominal Values (ppm/°C)*2	-	-55	_	·25	_	10
		Max.	Min.	Max.	Min.	Max.	Min.
2C	0± 60	0.82	-0.45	0.49	-0.27	0.33	-0.18
3C	0±120	1.37	-0.90	0.82	-0.54	0.55	-0.36
4C	0±250	2.56	-1.88	1.54	-1.13	1.02	-0.75
2P	-150± 60	_	_	1.32	0.41	0.88	0.27
3P	-150±120	_	_	1.65	0.14	1.10	0.09
4P	-150±250	_	_	2.36	-0.45	1.57	-0.30
2R	-220± 60	_	_	1.70	0.72	1.13	0.48
3R	-220±120	_	_	2.03	0.45	1.35	0.30
4R	-220±250	_	_	2.74	-0.14	1.83	-0.09
2S	-330± 60	_	_	2.30	1.22	1.54	0.81
3S	-330±120	_	_	2.63	0.95	1.76	0.63
4S	-330±250	_	_	3.35	0.36	2.23	0.24
2T	-470± 60	_	_	3.07	1.85	2.05	1.23
3T	-470±120	_	_	3.40	1.58	2.27	1.05
4T	-470±250	_	_	4.12	0.99	2.74	0.66
3U	-750±120	_	_	4.94	2.84	3.29	1.89
4U	-750±250	_	_	5.65	2.25	3.77	1.50

^{*2}Nominal values denote the temperature coefficient within a range of 20°C to 125°C (for Δ C)/85°C (for other TC).

Monolithic Ceramic Capacitors GR_R6/R7/F5/E4 (X5R/X7R/Y5V/Z5U)

High Dielectric Constant Type 100V

Part Number	TC Code	Rated Voltage (Vdc)	Capacitance*	Length L (mm)	Width W (mm)	Thickness T (mm)
GRM188R72A222KD01	X7R (EIA)	100	2200pF±10%	1.6	0.8	0.80
GRM188R72A332KD01	X7R (EIA)	100	3300pF±10%	1.6	0.8	0.80
GRM219R72A472KA01	X7R (EIA)	100	4700pF±10%	2.0	1.25	0.90
GRM219R72A682KA01	X7R (EIA)	100	6800pF±10%	2.0	1.25	0.90
GRM21BR72A103KA01	X7R (EIA)	100	10000pF±10%	2.0	1.25	1.25
GRM31MR72A333KA01	X7R (EIA)	100	33000pF±10%	3.2	1.6	1.15
GRM31MR72A473KA01	X7R (EIA)	100	47000pF±10%	3.2	1.6	1.15
GRM32NR72A683KA01	X7R (EIA)	100	68000pF±10%	3.2	2.5	1.35
GRM32NR72A104KA01	X7R (EIA)	100	0.1μF±10%	3.2	2.5	1.35
GRM43RR72A154KA01	X7R (EIA)	100	0.15μF±10%	4.5	3.2	1.80
GRM43RR72A224KA01	X7R (EIA)	100	22000pF±10%	4.5	3.2	1.80
GRM43DR72A474KA01	X7R (EIA)	100	0.47μF±10%	4.5	3.2	2.00
GRM55DR72A105KA01	X7R (EIA)	100	1μF ±10%	5.7	5.0	2.00
GRM188F52A472ZD01	Y5V (EIA)	100	4700pF +80%, -20%	1.6	0.8	0.80
GRM32NF52A104ZA01	Y5V (EIA)	100	10000pF +80%, -20%	3.2	2.5	1.35
GRM55RF52A474ZA01	Y5V (EIA)	100	0.47μF +80%, -20%	5.7	5.0	1.80

Monolithic Ceramic Capacitors GR_R6/R7/F5/E4 (X5R/X7R/Y5V/Z5U)

Thin Layer Large-Capacitance type

Part Number		Dime	nsions (mı	n)		
Part Number	L	W	T	e min.	g min.	_
GRM033	0.6 ±0.03	0.3 ±0.03	0.3 ±0.03	0.1 to 0.2	0.2	S
GRM155	1.0 ±0.05	0.5 ±0.05	0.5 ±0.05	0.15 to 0.3	0.4	2 2 2 2 2
GRM185	1.6 ±0.1	0.8 ±0.1	0.5 +0/-0.2	0.2 to 0.5	0.5	2020
GRM188	1.6 ±0.1	0.8 ±0.1	0.8 ±0.1	0.2 to 0.5	0.5	
GRM216			0.6 ±0.1			
GRM219	2.0 ±0.1	1.25 ±0.1	0.85 ±0.1	0.2 to 0.7	0.7	
GRM21B			1.25 ±0.1			
GRM316			0.6 ±0.1			
GRM319	3.2 ±0.15	1.6 ±0.15	0.85 ±0.1	0.3 to 0.8	1.5	e g e
GRM31M	1		1.15 ±0.1	0.3 10 0.8	1.5	14-14
GRM31C	3.2 ±0.2	1.6 ±0.2	1.6 ±0.2			
GRM32D	3.2 ±0.3	2.5 +0.2	2.0 ±0.2	0.3	1.0	
GRM32E	3.2 ±0.3	2.5 ±0.2	2.5 ±0.2	0.3	1.0	
GRM43D			2.0 ±0.2			
GRM43E	4.5 ±0.4	3.2 ±0.3	2.5 ±0.2	0.3	2.0	ļ.
GRM43S]		2.8 ±0.2			I - L W -I
GRM55F	5.7 ±0.4	5.0 ±0.4	3.2 ±0.2	0.3	2.0	

Part Number	TC Code	Rated Voltage (Vdc)	Capacitance*	Length L (mm)	Width W (mm)	Thickness T (mm)
GRM155R60J154KE01	X5R (EIA)	6.3	0.15μF±10%	1.0	0.5	0.50
GRM155R60J224KE01	X5R (EIA)	6.3	22000pF±10%	1.0	0.5	0.50
GRM155R60J334KE01	X5R (EIA)	6.3	0.33 μF±10%	1.0	0.5	0.50
GRM155R60J474KE19	X5R (EIA)	6.3	0.47μF±10%	1.0	0.5	0.50
GRM188R60J225KE01	X5R (EIA)	6.3	2.2μF ±10%	1.6	0.8	0.80
GRM219R60J475KE01	X5R (EIA)	6.3	4.7μF ±10%	2.0	1.25	0.90
GRM21BR60J106KE01	X5R (EIA)	6.3	10μF ±10%	2.0	1.25	1.25
GRM21BR60J106ME01	X5R (EIA)	6.3	10μF ±20%	2.0	1.25	1.25
GRM32DR60J226KA01	X5R (EIA)	6.3	22μF ±10%	3.2	2.5	2.00
GRM32ER60J476ME20	X5R (EIA)	6.3	47μF ±20%	3.2	2.5	2.50
GRM43SR60J107ME20	X5R (EIA)	6.3	100μF ±20%	4.5	3.2	2.80
GRM55FR60J107KA01	X5R (EIA)	6.3	100μF ±10%	5.7	5.0	3.20
GRM55FR60J107MA01	X5R (EIA)	6.3	100μF ±20%	5.7	5.0	3.20
GRM21BF50J106ZE01	Y5V (EIA)	6.3	10μF +80%, -20%	2.0	1.25	1.25

Note • This catalog has only typical specifications because there is no space for detailed specifications. Therefore, please approve our product specification or transact the approval sheet for product specification before ordering. Especially, please read rating and
 \(\triangle \) CAUTION (for storage and operating, rating, soldering and mounting, handling) in them to prevent smoking and/or burning, etc.
 You are able to read a detailed specification in the website (http://search.murata.co.jp/) before to require our product specification or to transact the approval sheet for product specification.

No.	Ite	em	Specifications		Te	est Method	
1	Operating Tempera Range	-	B1, B3, F1 : -25°C to +85°C R6 : -55°C to +85°C F5 : -30°C to +85°C C8 : -55°C to +105°C, C7 : -55°C to +125°C	Reference (B1, B3, F	Temperature : 25 1 : 20℃)	5°C	
2	Rated Vo	Itage	See the previous pages	The rated voltage is defined as the maximum voltage which may be applied continuously to the capacitor. When AC voltage is superimposed on DC voltage, V ^{P,P} or V ^{O,P} , whichever is larger, should be maintained within the rated voltage range.			
3	Appearar	nce	No defects or abnormalities	Visual insp	ection		
4	Dimensio	ns	Within the specified dimensions	Using calip	pers		
5	Dielectric	Strength	No defects or abnormalities	is applied l	should be observ between the term ne charge/dischar	inations for 1	
6	Insulation Resistant		More than 50Ω • F	not exceed 75%RH ma	ling the rated volta	age at Referen	ured with a DC voltage noe Temperature and ging, provided the A.
			Within the specified tolerance	The capac	itance should be	measured at F	
7	7 Capacitance		*Table 1				1.0±0.2Vrms 0.5±0.1Vrms
			B1, B3, R6, C7, C8 : 0.1 max. F1, F5 : 0.2 max.		hould be measure and voltage show		ce Temperature at the
8	8 Dissipation Factor (D.F.)		*Table 1 GRM155 B3/R6 1A 124 to 224 GRM185 B3/R6 1A 105 GRM188 B3/R6 1C/1A 225 GRM219 B3/R6 1A 475 GRM21B B3/R6 1C/1A 106	C≦10 C≤10 C>10 *1 Ho			1.0±0.2Vrms 0.5±0.1Vrms
	No		B1, B3: Within +/-10% (-25°C to +85°C) F1 : Within +30/-80% (-25°C to +85°C) R6 : Within +/-15% (-55°C to +85°C) F5 : Within +22/-82% (-30°C to +85°C) C7 : Within +/-22% (-55°C to +125°C) C8 : Within +/-22% (-55°C to +105°C)	each spec The range Reference shown in the In case of measured equilibration	ified temp. stage. s of capacitance Temperature val he table should be	change compa ue over the te e within the sp the capacitan with applying stage.	mperature ranges becified ranges.* Ice change should be voltage in
				Step	Temperatu		Applying Voltage (V)
				1	Reference Ten		[[]g . onago (v)
9	Capacitance Temperature			2	-55±3 (for Ri -25±3 (for Bi -30±3 (f	31, B3, F1)	
	Characteristics			3	Reference Ten	npereture±2	No bias
		50% of the Rated	B1: Within +10/-30%	4	85±3 (for B1, B3 125±3 (for 105±3 (for	or C7)/	
		Voltage	F1: Within +30/-95%	5	20±	:2	
		390		6	-25±3 (for	B1, F1)	50% of the rated
				7	20±		voltage
				8	85±3 (for		1
				Perform a then set fo	asurement for hig heat treatment at r 48±4 hours at r e initial measurer	150 +0/-10° com temperat	C for one hour and



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No.	Item	Specifications	Test Method				
		No removal of the terminations or other defects should occur	Solder the capacitor on the test jig (glass epoxy board) shown in Fig. 1a using an eutectic solder. Then apply 10N* force in parallel with the test jig for 10+/−1sec. The soldering should be done either with an iron or using the reflow method and should be conducted with care so that the soldering is uniform and free of defects such as heat shock. *5N: GR□15/GRM18, 2N: GR□33				
10	Adhesive Strength of Termination	Solder resist Baked electrode or copper foil Fig. 1a	Type a b c GR□03 0.3 0.9 0.3 GR□15 0.4 1.5 0.5 GRM18 1.0 3.0 1.2 GRM21 1.2 4.0 1.65 GRM31 2.2 5.0 2.0 GRM32 2.2 5.0 2.9 GRM43 3.5 7.0 3.7 GRM55 4.5 8.0 5.6				
	Appearance	No defects or abnormalities	Solder the capacitor on the test jig (glass epoxy board) in the				
11	Capacitance Vibration D.F.	Within the specified tolerance B1, B3, R6, C7, C8: 0.1 max. F1, F5: 0.2 max.	same manner and under the same conditions as (10). The capacitor should be subjected to a simple harmonic motion having a total amplitude of 1.5mm, the frequency being varied uniformly between the approximate limits of 10 and 55Hz. The frequency range, from 10 to 55Hz and return to 10Hz, should be traversed in approximately 1 minute. This motion should be applied for a period of 2 hours in each 3 mutually perpendicular directions (total of 6 hours).				
12	Deflection	No cracking or marking defects should occur 20 50 Pressunzing speed: 1.0mm/sec. Pressunze R230 Capacitance meter 45 45	Solder the capacitor on the test jig (glass epoxy board) shown in Fig. 2a using an eutectic solder. Then apply a force in the direction shown in Fig. 3a for 5+/-1 sec. The soldering should be done either with an iron or using the reflow method and should be conducted with care so that the soldering is uniform and free of defects such as heat shock. The soldering is uniform and free of defects such as heat shock.				
			(GR□03, GR□15 : t : 0.8mm) Type a b c				
		Fig.3a	GR□03 0.3 0.9 0.3 GR□15 0.4 1.5 0.5 GRM18 1.0 3.0 1.2 GRM21 1.2 4.0 1.65 GRM31 2.2 5.0 2.0 GRM32 2.2 5.0 2.9 GRM43 3.5 7.0 3.7 GRM55 4.5 8.0 5.6 (in mm)				
13	Solderability of Termination	75% of the terminations is to be soldered evenly and continuously	Immerse the capacitor in a solution of ethanol (JIS-K-8101) and rosin (JIS-K-5902) (25% rosin in weight propotion) . Preheat at 80 to 120° C for 10 to 30 seconds. After preheating, immerse in an eutectic solder solution for $2+/-0.5$ seconds at $230+/-5^{\circ}$ C.				



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No.	Item	Specifications		Tes	st Metho	d			
	Appearance Capacitance Change		Preheat the capacitor at 120 to 150°C for 1 minute. Immerse the capacitor in an eutectic solder solution at 270+/-5°C for 10+/-0.5 seconds. Set at room temperature fo 24+/-2 hours (temperature compensating tyoe) or 48+/-4 hours (high dielectric constant type), then measure.						
	Q/D.F.	F1, F5 : 0.2 max.							
Resistar	I.R.	More than 50Ω • F		ç constant type 10℃ for one ho					
Solderin Heat	g Dielectric Strength	No defects		om temperature itial measurem		/-4 hours.			
			*Preheating fo	or GRM32/43/5	5				
			Step	-	erature		me		
			1		to 120℃	-	min.		
			2	170℃	to 200℃	11	min.		
	Appearance	No defects or abnormalities				in the same m	anner and		
	Capacitance Change	B1, B3, R6, C7, C8 : Within ±7.5% F1, F5 : Within ±20%	Perform the fi	ne conditions a ve cycles acco following table.	rding to t	the four heat tre	eatments		
	D.F.	B1, B3, R6, C7, C8 : 0.1 max. F1, F5 : 0.2 max.	Set for 24+/- 48+/-4 hours						
	I.R.	More than 50Ω • F	temperature, t	then measure.					
Temperati Sudden Change	Dielectric Strength	No defects	Step	1 Min.	2 Room	3 Max.	4 Room		
Change			Temp. (°C)	Operating Temp. +0/-3 30±3	Temp.	Operating Temp. +3/-0 30±3	Temp.		
	Appearance	No defects or abnormalities	then set at roo Perform the in	om temperature itial measurem	e for 48+, nent.	10℃ for one ho /—4 hours.			
	Capacitance Change					ge currentis les			
High Temperate High Humidity	D.F.	B1, B3, R6, C7, C8 : 0.2 max. F1, F5 : 0.4 max. More than 12.5Ω • F		it treatment at 48+/-4 hours	treatment at 150+0/-10°C for one hour and 8+/-4 hours at room temperature. Perform th				
(Steady)			Perform a hea	 Measurement after test Perform a heat treatment at 150+0/−10°C for one hour and then let sit for 48+/−4 hours at room temperature, then measure. 					
	Appearance	No defects or abnormalities			-	000+/-12 hou			
	Capacitance Change	B1, B3, R6, C7, C8 : Within ±12.5% F1, F5 : Within ±30%	hours at room	rating tempera temperature, t ischarge curre	hen mea		18+/-4		
	D.F.	B1, B3, R6, C7, C8 : 0.1 max. F1, F5 : 0.4 max.	•Initial measu	rement					
7 Durabili	I.R.	More than 25Ω • F		48+/-4 hours		10℃ for one ho temperature. P			
				it treatment at		10℃ for one ho temperature, th			